

Formation of amorphous Al₂O₃ phase on aluminum alloy by *in-situ* laser cladding

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It is well known that amorphous materials have excellent mechanical, physical and chemical properties, and thus, synthesizing an amorphous layer on crystalline substrates can significantly improve the surface performances of the substrate material. Surface amorphization can be achieved by laser surface treatment due to the rapid heating and cooling characteristics of laser treatment, which inhibit long-range diffusion and prevent crystallization. Amorphous layers and amorphous-crystalline coexisting layers have been obtained by various laser surface treatment techniques, such as the laser direct remelting of substrate materials [1, 2]; laser remelting of plasma-sprayed coatings [3]; laser remelting of laser-clad coatings [4]; laser alloying [5]; laser cladding of high glass-forming ability powders [6] and laser-induced self-propagating reactions [7]. The present paper describes the synthesis of the Al₂O₃ amorphous phase on aluminum alloy 7075 by the method of *in-situ* laser cladding through the thermite reaction between CuO and Al powders.

The mixed powders of CuO(3 mol) + Al(2 mol) + SiO₂(3 mol) were pre-placed on an Al-7075 alloy substrate using a pasting binder. The nominal mesh size of the powders was 200, which is equivalent to a particle size of 70 μm; the thickness of pre-placement was approximately 0.5 mm. A high-power PRC CW-CO₂ laser was employed for track melting under an Ar-shielding atmosphere. The diameter of the laser spot and the laser power were kept constant at 2 mm and 1800 W, respectively; whereas a laser-scanning velocity of 25 mm/s, and a 50% track-overlapping condition were used. The substrate was water-cooled during the laser cladding. SiO₂ powders were used to slow down the exothermic reaction, since it was found that a mole ratio of 2Al:3CuO would result in violent reactions.

The different phases of the clad layer were determined with an X-ray diffraction technique using Cu-K_α radiation at 40 KV and 30 mA (Philips PW-3710), energy dispersive X-ray spectroscopy (EDX) and transmission electron microscopy (Jeol 2010). Cross-sectional specimens were prepared for the TEM and high-resolution TEM study (HRTEM). The TEM specimens were mechanically ground and polished to a thickness of about 30 μm. This was followed by ion milling, which used Ar⁺ bombardment at 5 keV using a Gatan Precision Polishing System.

Fig. 1 shows a typical microstructure of the clad layer, which clearly shows two distinct zones: the Al₂O₃ reaction layer (R) and the fusion layer (F). Fig. 2 shows

the XRD results of the clad layer, which show that the α-Al₂O₃, γ-Al₂O₃, Al₂Cu and Cu₂O phases are present in the laser-processed zone.

At the top of the Al₂O₃ reaction layer (Fig. 3), a complete amorphous structure of Al₂O₃ phase is present (labelled A); underneath it, a structure consisting of an amorphous Al₂O₃ phase and fine crystallines of γ-Al₂O₃ (labelled B) is found. This is followed by a structure composed of a metastable γ-Al₂O₃ phase (labelled C). The compositions of the various phases found in locations A, B, and C are present in Table I. The outermost layer of the reaction zone is confirmed to have an amorphous structure based on the broadened halo configurations of the selected-area electron diffraction (SAED) patterns (Fig. 4) and the lattice image of amorphous structures (Fig. 5). The XRD results did not show any obvious peaks for the amorphous phase. This could be due to the amount of the phase which is below the detection limit of the technique. The SAED pattern for structure B consists of broadened halos and diffraction spots from [001] of the γ-Al₂O₃ phase (Fig. 6). The SAED pattern for the metastable γ-Al₂O₃ phase of structure C is shown in Fig. 7, a dark field image of which is shown in Fig. 8. It is estimated that the thickness of the amorphous Al₂O₃ zone is about 500 nm, while the thickness of zone B is some 50–150 nm, and the size of the γ-Al₂O₃ crystallines is about 600 nm.

It is well known that glass forming ability is governed by the chemical composition of the molten pool and the cooling rate of the melts. In the present study, the formation of the amorphous Al₂O₃ phase is considered to be due to the high cooling rate of the Al₂O₃ melt and to the presence of the reduced metalloid Si. The mechanism of *in-situ* laser cladding is highly complex, especially when thermite reactions are involved. Nonetheless, an estimation of the cooling rates, $\partial T/\partial t$, for *in-situ* laser cladding at high scanning speeds can be made using the Rosenthal solution for a moving heat point source [4]:

$$\partial T/\partial t = -2\pi\kappa \times (V/P) \times (\Delta T)^2 \quad (1)$$

where κ is the thermal conductivity, V is the scanning speed, P is the absorbed laser power which is equal to $P_{\text{total}}(1 - R)$, R is the fraction of reflection, and ΔT is the range of temperature variation during cooling. In the calculation, it is assumed that the maximum temperature in the clad pool is lower than that of the boiling temperature of Al₂O₃, and is higher than that of

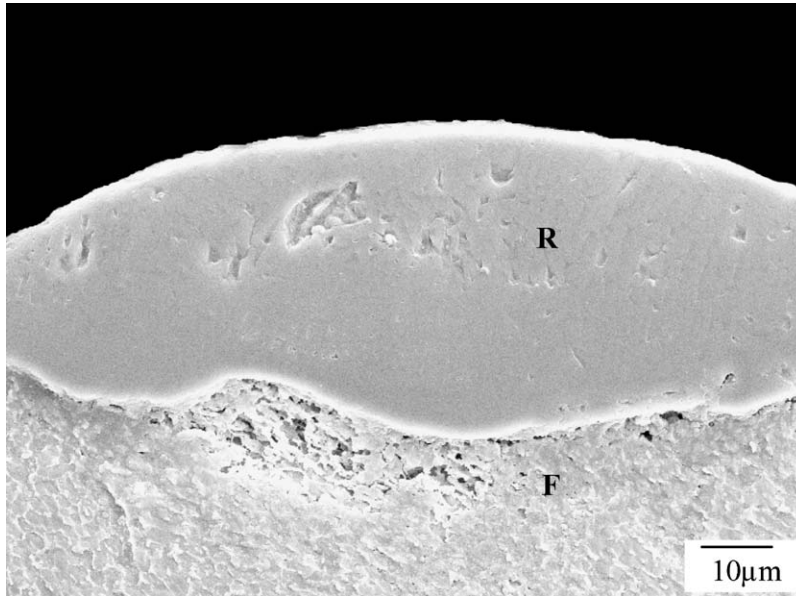


Figure 1 An SEM photo showing the Al₂O₃ reaction layer (R) and the fusion layer (F) (etched in Keller's reagent).

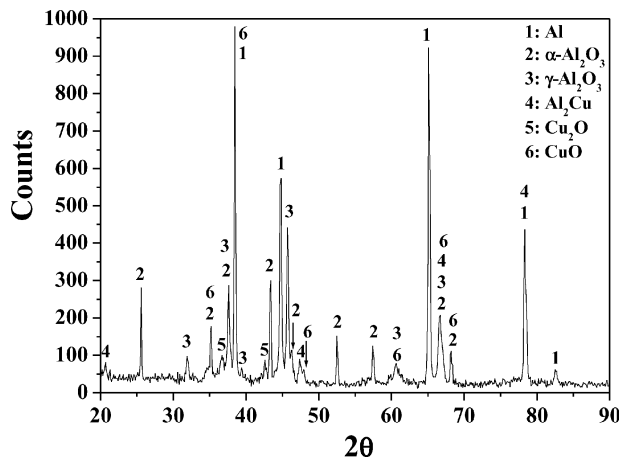


Figure 2 The XRD results of the clad layer.

TABLE I The EDX results for locations A, B and C

Location	Al (at.%)	O (at.%)
A	46.78	53.22
B	33.70	66.30
C	43.92	56.08

the melting temperature of Al₂O₃, given the realization that the heat generated by the thermite reaction of 3CuO + 2Al → Al₂O₃ + 3Cu is high enough to heat up the reaction products of 3 mol Cu and 1 mol Al₂O₃ from the reaction temperature (1133 K) to the melting temperature of Al₂O₃ (2327 K). Table II presents the results of the calculated cooling rates for Al₂O₃ under the laser cladding condition of this study. The

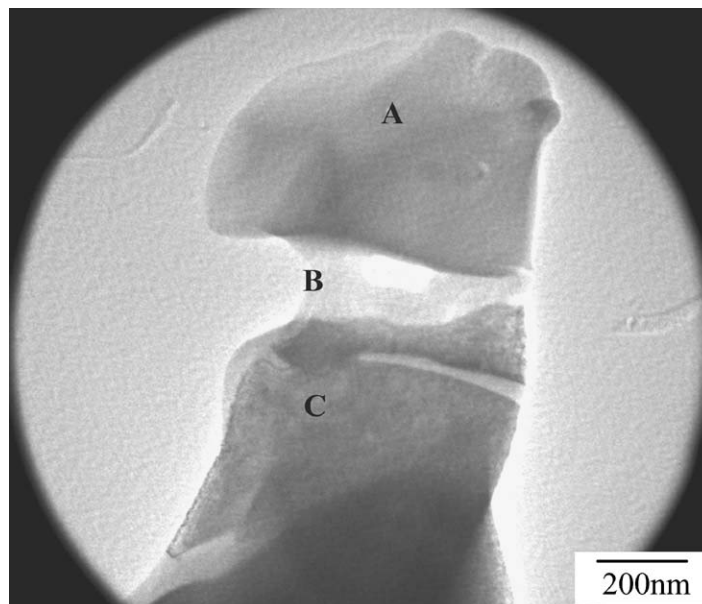


Figure 3 A TEM bright field image of the top surface of the reaction layer.

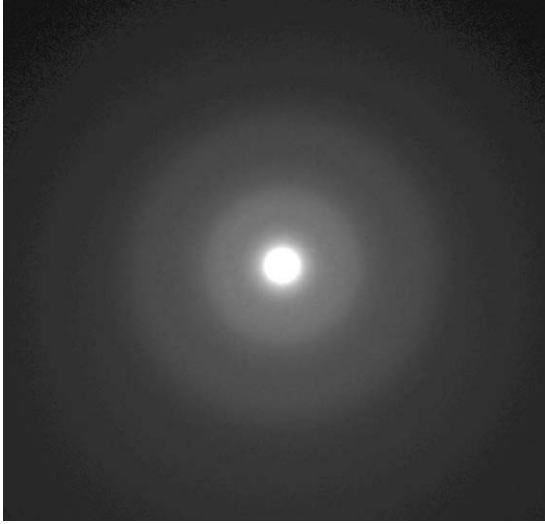


Figure 4 The diffraction pattern of the amorphous Al_2O_3 phase at location A in Fig. 3.

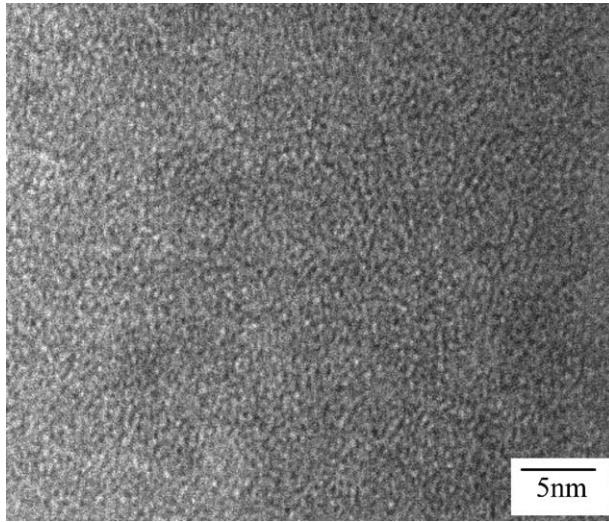


Figure 5 A high-resolution TEM image of the structure at location A.

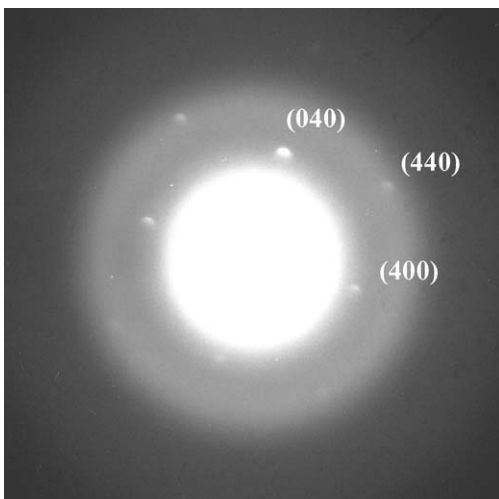


Figure 6 The diffraction pattern of the amorphous Al_2O_3 phase coexisting with crystallines of $\gamma\text{-Al}_2\text{O}_3$ at location B.

results show that the cooling rate of the Al_2O_3 phase is in the order of $10^3\text{--}10^4\text{K/s}$, which is similar to that obtained by other studies on laser surface treatments [2, 8]. This cooling rate is believed to be high enough

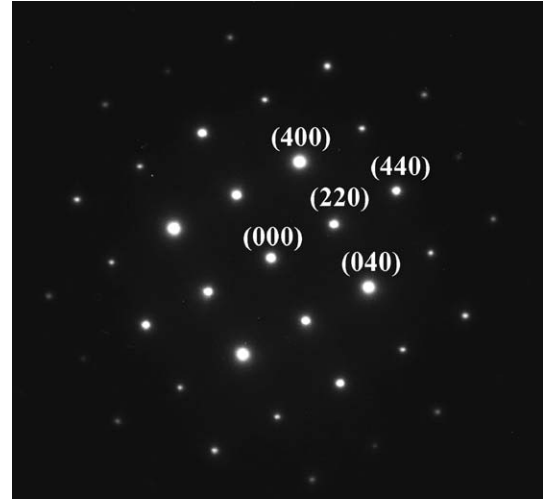


Figure 7 The electron diffraction pattern from [001] of the $\gamma\text{-Al}_2\text{O}_3$ phase at location C.

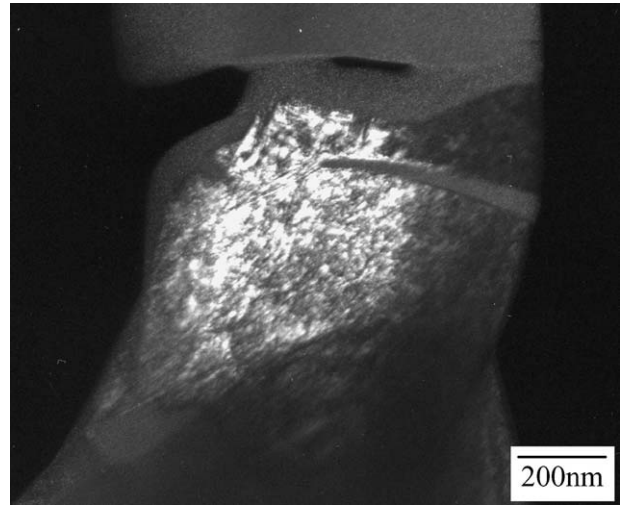


Figure 8 A dark field image of spot (040) shown in Fig. 7.

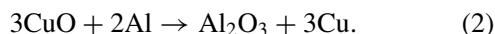
to allow the metastable $\gamma\text{-Al}_2\text{O}_3$ phase to form, since it was reported that a cooling rate in the order of 400K/s is enough to form the $\gamma\text{-Al}_2\text{O}_3$ phase [9]. Moreover, Cao [10] believed that if the cooling rate was high enough, the long-range order of the $\gamma\text{-Al}_2\text{O}_3$ phase could break up entirely and an amorphous Al_2O_3 structure could be produced. In fact, during the solidification of the laser melt pool, the temperature gradient (G) at the solidification front will steadily decrease from the bottom of the melt to the top surface, and the solidification rate (V) of the melt-liquid interface will increase from zero at the bottom to a maximum at the top surface. That means that the cooling rate (R) will increase from the bottom of the melt to the top surface of the clad layer according to the relationship of $R = GV$. In other words, the top surface layer will experience the highest cooling rate

TABLE II The laser parameters and the calculated cooling rates

P (W)	1080
V (m/s)	0.025
κ (W/m \cdot K) [16]	7.1128–25.104
ΔT (K)	2029
$-\partial T/\partial t$ (K/s)	$4.26 \times 10^3\text{--}1.5 \times 10^4$

and, as a result, an amorphous Al₂O₃ phase could form at the outermost surface of the Al₂O₃ reaction layer.

However, a fast cooling rate alone may not be good enough for the amorphous Al₂O₃ phase to form under the conditions of this study. A parallel study shows that when the laser cladding experiment was performed without SiO₂ powders, no amorphous phase was detected. It is considered that when SiO₂ powders are present in the pre-mixed cladding powders, they can react with the molten aluminum. When the pre-placed powder mix, which is composed of SiO₂, is irradiated by the laser light, a thermite reaction between CuO and Al powders is initiated when the temperature is raised to about 1133 K [11],



Notwithstanding the short interaction time between the laser light and the coating, it is considered that the melting of the pre-placed coating started with the aluminum powders, which have a relatively low melting point. Therefore, apart from the above thermite reaction, SiO₂ can react with molten aluminum according to the following reaction: $3\text{SiO}_2 + 4\text{Al} \rightarrow 3\text{Si} + 2\text{Al}_2\text{O}_3$. As a result, silicon is produced. Previous studies have shown that silicon can improve the thermal stability of the supercooled liquid and enhance the glass-forming ability of some metallic glass-forming alloys [12, 13]. This was considered to be attributed to the neutralizing effect of nucleation sites by silicon. On the other hand, Li [14] believed that the addition of elements with small-sized atoms, such as C, B and Si, can increase the degree of disorder of the atoms in glass-forming alloys, and consequently improve the amorphous forming ability of the alloy. In the present study, the exact role of silicon in promoting the formation of the amorphous Al₂O₃ phase is still unclear, and further research is required. It should be pointed out that no silicon was detected by the energy disperse X-ray (EDX) analysis within the locations of A, B, and C. This could be because the amount present was below the detection limit. The limits of solubility of silicon in Al₂O₃ are 220 and 300 ppm at 1773 and 1873 K, respectively [15].

Acknowledgments

This work was fully supported by the Research Grants Council of the Hong Kong Special Administrative Region, China (Project no. PolyU5194/02E). The authors are grateful to Dr G. K. H. Pang of the Department of Applied Physics for his assistance in performing the TEM work. The infra-structural support provided by PolyU is also acknowledged.

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Received 6 May
and accepted 20 May 2004